Crystal Quality of 3C-SiC Influenced by the Diffusion Step in the Modified Four-Step Method

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The atomic arrangement and bonding characteristics of void-free 3C-SiC grown by the modified four-step method are presented. Without the diffusion step, Si–C bonds are partially formed in the as-carburized layer on Si(100). The ratio of C–C bonds to Si–C bonds is about 7:3, which can be lowered to about 1:9 after the diffusion step at 1350°C for 5 min or at 1300°C for 7 min according to C 1s core level spectra. The residual C–C bonds cannot be removed, which is associated with an irregular atomic arrangement (amorphous) located either at the 3C-SiC/Si(100) interface or at the intersection of twin boundaries in the 3C-SiC buffer layer based on the lattice image taken by transmission electron microscope. The diffusion step helps the formation of Si–C bonds more completely and results in a SiC buffer layer of high quality formed on Si(100) before the growth step. However, twins and stacking faults still appear in the 3C-SiC buffer layer after the diffusion step. The formation mechanism of the 3C-SiC buffer layer is proposed and discussed.

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Silicon carbide (SiC) is a wide bandgap semiconductor for high power and high frequency devices due to its excellent thermal and electrical characteristics." As a means to lower the production cost, the heteroepitaxy of 3C-SiC on Si has attracted attention in the past decades. The difficulty to grow a 3C-SiC layer of good quality on Si arises from large lattice mismatch (~20%) and difference in thermal expansion coefficients (~8%). The breakthrough in the growth of 3C-SiC on Si using a buffer layer was first reported by Nishino et al." A conventional three-step method, consisting of cleaning, carburization, and growth, was proposed and illustrated. The carburization step plays two roles in the growth of 3C-SiC on Si in the conventional three-step method. One is to supply carbon atoms in the form of amorphous carbon onto Si at carburization temperature, and the formation step plays two roles in the growth of 3C-SiC on Si in the conventional three-step method. The other is to supply carbon atoms in the form of amorphous carbon onto Si at carburization temperature, usually at 1250°C for the C4H8/H2/SiH4 system. The other is to form a 3C-SiC buffer layer by driving Si atoms out of the Si substrate into the amorphous carbon layer at carburization temperature. The carburization step has become a standard procedure for the growth of 3C-SiC on Si since then." However, voids" and micropipes" which are attributed to the out-diffusion of Si atoms, appear at the 3C-SiC/Si interface after carburization. In addition to voids and micropipes, planar defects such as twins and stacking faults are generated in the 3C-SiC buffer layer as a result of the strain relaxation at the lattice-mismatched SiC/Si interface. The planar defects are generated and propagated along the [111] planes in 3C-SiC grown on Si, which usually occurs at a high heating rate and a low partial gas pressure of carbon, reported by Cimalla et al. and Yun et al."

The conventional three-step method is a long time process because it requires cooling the samples back to room temperature between each step. It takes about 1 h to cool the sample from process temperature to room temperature in each step. The conventional three-step method can be performed either by atmospheric pressure chemical vapor deposition (APCVD) or by low pressure chemical vapor deposition (LPCVD). Zorman et al. showed in 1995 that the void-free growth of 3C-SiC films on a large area of Si substrates was achieved by APCVD using the conventional three-step process. However, two major issues associated with the LPCVD growth of 3C-SiC epitaxial films using the conventional three-step method remain to be solved. One is the voids at the SiC/Si interface because the out-diffusion of Si atoms is severe in LPCVD. The other is the planar defects (twins and stacking faults) generated in the 3C-SiC buffer layer due to the lattice-mismatch-induced stress at the SiC/Si interface.

In 2008, Chen et al. developed the modified four-step method (cleaning, carburization, diffusion, and growth) associated with the LPCVD growth by inserting a diffusion step and by removing the cooling step in the conventional three-step method. The modified four-step method can be performed in a shorter time than the conventional three-step method because the out-diffusion of Si atoms is severe in LPCVD. The other way to voids at the SiC/Si interface.

In this paper, we present the variation in structural and bonding characteristics of the 3C-SiC buffer layer grown on Si(100) by LPCVD at different diffusion temperatures and times. The formation mechanism of the 3C-SiC buffer layer is also proposed to explain the out-diffusion of Si atoms from the deposition of amorphous carbon. However, the atomic arrangement and bonding characteristics of the 3C-SiC buffer layer are unclear.

In the Experimental section, we present the variation in structural and bonding characteristics of the 3C-SiC buffer layer grown on Si(100) by LPCVD at different diffusion temperatures and times. The formation mechanism of the 3C-SiC buffer layer is also proposed to explain the out-diffusion of Si atoms from the deposition of amorphous carbon. However, the atomic arrangement and bonding characteristics of the 3C-SiC buffer layer are unclear.

A horizontal cold-wall-type LPCVD system with induction heating was used for the growth of 3C-SiC on a p-type Si(100) substrate, which was illustrated previously by other groups. The Si(100) substrate of 1 x 1 cm was dipped in 1% HF for 30 s, rinsed by deionized water, and then placed on a SiC-coated graphite susceptor that was heated by radio-frequency induction. The mixed gas of SiH4 (5% in H2) and C2H6 (4N) was carried by H2 (5N) into the LPCVD chamber for the growth of 3C-SiC on Si(100). The temperature was ramped up at a rate of about 11°C/s and measured by a thermocouple and an IR pyrometer. The total pressure was varied by controlling the throttle valve between the LPCVD chamber and the mechanical pump. Most samples were treated with the modified four-step method shown in Fig. 1a. Some samples were treated with the modified four-step method without the growth step shown in Fig. 1b for comparison.

The optimum experimental parameters for the modified four-step method listed in Table 1 were reported in our previous work. The growth rate of 3C-SiC was approximately 3 μm/h, and all the 3C-
SiC film thicknesses were kept at 1.5 μm in this study. The structural information of 3C-SiC films was characterized using a Rigaku D/MAX2000 X-ray diffractometer (XRD) with a Cu Kα radiation (1.5405 Å) and an FEI TECNAI G2 transmission electron microscope (TEM). The bonding characteristics of 3C-SiC films were characterized using X-ray photoelectron spectroscopy (XPS, PHI ESCA 1600).

**Results and Discussion**

The crystal qualities of 3C-SiC films grown on Si(100) using the modified four-step method are strongly affected by temperature and process time at the diffusion step, as shown in the XRD spectra in Fig. 2a and b. Only the (200) peak of 3C-SiC increases in intensity with process time at 1300°C, as shown in Fig. 2a. The role of the diffusion step at 1300°C is to assist the growth of 3C-SiC films of good quality before the growth step. When the temperature is raised from 1300 to 1350°C, a higher intensity of 3C-SiC(200) can be achieved at a shorter process time. The improvement of the crystal qualities of the 3C-SiC films by the diffusion step is also confirmed by X-ray rocking curve measurements. The full width at half-maximum (fwhm) of 3C-SiC(200) reduces from 0.77 to 0.73 and from 0.77 to 0.67 by treating samples with the diffusion step at 1300 and 1350°C for 9 min, respectively, as listed in Table II. A better crystal quality of the 3C-SiC film can be obtained within a shorter process time at a higher temperature.

The quality improvement of the SiC buffer layer is further investigated by XPS and TEM for the as-diffused 3C-SiC/Si(100) samples (grown by the modified four-step method without the growth step in our LPCVD system). The Si–C bond formation of the as-diffused 3C-SiC/Si(100) samples is clearly illustrated by the curve-fit of the C 1s core level spectra in Fig. 3a and b. All the Si(100) samples are carburized at a C₃H₈ partial pressure of 1.9 × 10⁻² Torr and at 1250°C for 1.5 min before treating with the diffusion step at 1300 or 1350°C. There exists a broad shoulder (or peak) on the left side of the prominent C 1s peak at ~283 eV, indicating the existence of two types of carbon bonding environments in the 3C-SiC buffer layer after diffusion. The two C 1s components located at 284.5 and 283.2 eV are required to obtain consistent curve-fit results, which are assigned as C–C and Si–C bonds, respectively. The difference in the C 1s binding energies of the C–C and Si–C bonds results from the different amounts of charge transfer. The corresponding curve-fit results are also listed in Table II. The ratio of Si–C bonds to C–C bonds for the as-carburized 3C-SiC/Si(100) sample is about 3:7, suggesting that Si–C bonds form partially at the carburization step. In other words, the Si atoms diffused out of Si(100) are not enough to transform the as-carburized layer into SiC and result in excess carbon (C–C bonds) that resided in the as-carburized Si(100) layer. The excess carbon

### Table I. Optimal experimental parameters at each step in the modified four-step method.

<table>
<thead>
<tr>
<th>Clean</th>
<th>Carburization</th>
<th>Diffusion</th>
<th>Growth</th>
</tr>
</thead>
<tbody>
<tr>
<td>H₂ (scm)</td>
<td>1000</td>
<td>1000</td>
<td>1000</td>
</tr>
<tr>
<td>C₃H₈ (scm)</td>
<td>0</td>
<td>10</td>
<td>0</td>
</tr>
<tr>
<td>SiH₄ (scm)</td>
<td>0</td>
<td>0</td>
<td>0</td>
</tr>
<tr>
<td>Temperature (°C)</td>
<td>900</td>
<td>1250</td>
<td>1350</td>
</tr>
<tr>
<td>Pressure (Torr)</td>
<td>10</td>
<td>2</td>
<td>2</td>
</tr>
</tbody>
</table>

*Data extracted from the C 1s core level spectra for the sample without the diffusion treatment.*

### Table II. FWHM of the SiC(200) peak and the area percentages of the C–C and C–Si bonds deconvoluted from C 1s core level spectra taken from the samples treated with different diffusion conditions (temperature and process time).

<table>
<thead>
<tr>
<th>Diffusion temperature (°C)</th>
<th>Diffusion time (min)</th>
<th>fwhm (°)</th>
<th>C–C (%)</th>
<th>C–Si (%)</th>
</tr>
</thead>
<tbody>
<tr>
<td>1300</td>
<td>0</td>
<td>0.77</td>
<td>69¹</td>
<td>31¹</td>
</tr>
<tr>
<td>1300</td>
<td>1</td>
<td>0.76</td>
<td>48</td>
<td>52</td>
</tr>
<tr>
<td>1300</td>
<td>3</td>
<td>—</td>
<td>27</td>
<td>73</td>
</tr>
<tr>
<td>1300</td>
<td>5</td>
<td>0.74</td>
<td>19</td>
<td>81</td>
</tr>
<tr>
<td>1300</td>
<td>7</td>
<td>—</td>
<td>8</td>
<td>92</td>
</tr>
<tr>
<td>1350</td>
<td>9</td>
<td>0.73</td>
<td>8</td>
<td>92</td>
</tr>
<tr>
<td>1350</td>
<td>0</td>
<td>0.77</td>
<td>69¹</td>
<td>31¹</td>
</tr>
<tr>
<td>1350</td>
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<td>0.71</td>
<td>36</td>
<td>64</td>
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<tr>
<td>1350</td>
<td>3</td>
<td>—</td>
<td>19</td>
<td>81</td>
</tr>
<tr>
<td>1350</td>
<td>5</td>
<td>0.67</td>
<td>10</td>
<td>90</td>
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<tr>
<td>1350</td>
<td>7</td>
<td>—</td>
<td>8</td>
<td>92</td>
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<tr>
<td>1350</td>
<td>9</td>
<td>0.67</td>
<td>7</td>
<td>93</td>
</tr>
</tbody>
</table>

¹Data extracted from the C 1s core level spectra for the sample without the diffusion treatment.*
results from the carbon deposition at a high C\textsubscript{3}H\textsubscript{8} flow rate (10 sccm) that is designed to cover the Si(100) surface quickly to avoid the interfacial void formation at the carburization step. The as-carburized Si(100) surface with excess carbon can be further transformed into a SiC buffer layer at the diffusion step before the growth step. After diffusion at 1300°C, the amount of Si–C bonds increases with process time and reaches a maximum value at approximately 7 min, accompanied with the reduction in C–C bonds. The highest ratio of Si–C bonds to C–C bonds is about 9:1. The ~10% excess carbon (C–C bonds) still resides in the SiC buffer layer, which is probably located at the intersection of twins that are illustrated in TEM micrographs and discussed later. A similar result occurs at a faster rate for the diffusion step at 1350°C. The relative amount of Si–C bonds increases with process time and reaches a maximum value at approximately 5 min, as indicated in Table II. The faster increase rate of Si–C bonds at 1350°C indicates that the Si–C bond formation in the SiC buffer layer is controlled by a diffusion-limited process. The Si–C bond formation in the SiC buffer layer enables the growth of a SiC film of better quality at the growth step, supporting the fact that SiC nuclei grow in size by forming Si–C bonds more completely. The TEM image indicates that the SiC layer is in an epitaxial orientation relationship. The TEM image III with sharp spots is determined to be the ED pattern of Si. The three FFT images and the lattice image in Fig. 4b support that the ultrathin SiC layer is single-crystalline. However, some planar defects and irregular atomic arrangements exist in the 3C-SiC buffer layer.

The formation of the SiC buffer layer at carburization and diffusion steps is proposed and described as follows: First, the amorphous carbon is deposited on Si(100) and partially reacted with Si atoms to form Si–C bonds when a high flow rate (10 sccm) of C\textsubscript{3}H\textsubscript{8} is introduced into the LPCVD chamber at the carburization step. The ratio of C–C bonds to Si–C bonds is about 7:3, right after the carburization step, according to the XPS data. There should be a SiC nuclei dispersed in a matrix of amorphous carbon after the carburization step because the volume ratio of C–C bonds is very large (~ 70%). Second, the diffusion step assists in the Si–C bond formation more completely. The TEM image indicates that the SiC layer is finally in a crystal form on Si(100) after the diffusion step. This supports the fact that SiC nuclei grow in size by forming Si–C bonds via the out-diffusion of Si atoms toward the amorphous carbon layer. The out-diffusion of Si atoms stops, and the ratio of the C–C bonds to Si–C bonds reaches ~1.9 after the diffusion step. A continuous SiC buffer layer is finally formed on Si(100). The residual C–C bonds are probably associated with irregular atomic arrangements, which are located either at the 3C-SiC/Si(100) interface or at the intersection of twin boundaries shown in the TEM lattice image in Fig. 4b.

Conclusions

A void-free 3C-SiC/Si(100) interface can be achieved by LPCVD using the modified four-step method. The formation of Si–C bonds is not sufficient at the carburization step. The 3C-SiC nuclei are dispersed in a matrix of amorphous carbon after the car-
burization step. The diffusion step helps the formation of Si–C bonds more completely before the growth of 3C-SiC. A 3C-SiC buffer layer of high quality is formed on Si(100) after the diffusion step. However, twins and stacking faults, resulting from the relaxation of strain, cannot be removed after the diffusion step.

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